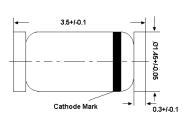
Silicon Epitaxial Planar Switching Diode

Features

- Lead Free
- Fast switching speed
- High reliability
- High conductance
- For general purpose switching applications





Glass case MiniMELF Dimensions in mm

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	50	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Forward Continuous Current	I _{FM}	300	mA
Power Dissipation	P _{tot}	500	mW
Junction temperature	Tj	175	C°
Storage Temperature Range	T _{stg}	- 65 to +175	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{ extsf{ heta}JA}$	300	°C/W

Characteristics at T_a = 25°C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	1.2	V
Reverse Current at V _R = 50 V	I _R	100	nA
Reverse Recovery Time at I _F = I _R = 10 to 200 mA, to 0.1 I _F	t _{rr}	4	ns

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